HMC441LC3B* PRODUCT PAGE QUICK LINKS

Last Content Update: 10/05/2017

COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

EVALUATION KITS

• HMC441LC3B Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

 HMC441LC3B: GaAs pHEMT MMIC Medium Power Amplifier, 6 - 18 GHz Data Sheet

TOOLS AND SIMULATIONS 🖵

HMC441LC3B S-Parameters

REFERENCE MATERIALS 🖳

Quality Documentation

- Package/Assembly Qualification Test Report: LC3, LC3B, LC3C (QTR: 2014-00376 REV: 01)
- Semiconductor Qualification Test Report: PHEMT-F (QTR: 2013-00269)

DESIGN RESOURCES 🖵

- HMC441LC3B Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

DISCUSSIONS

View all HMC441LC3B EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT 🖳

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK 🖳

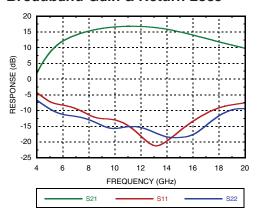
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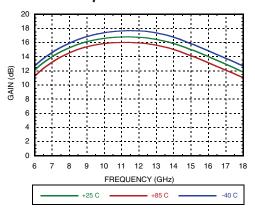


GaAs pHEMT MMIC MEDIUM POWER AMPLIFIER, 6 - 18 GHz

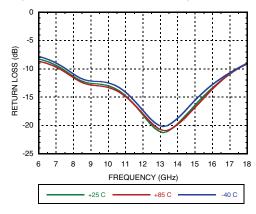
Broadband Gain & Return Loss



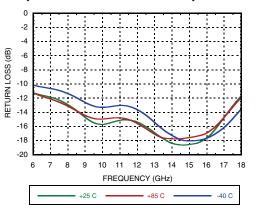
Gain vs. Temperature



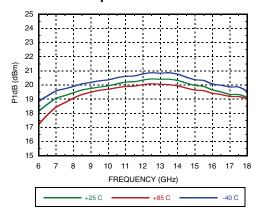
Input Return Loss vs. Temperature



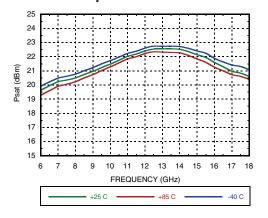
Output Return Loss vs. Temperature



P1dB vs. Temperature



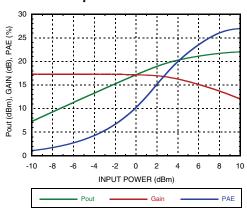
Psat vs. Temperature



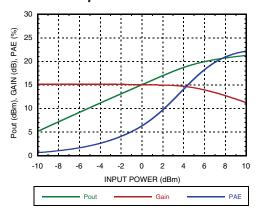


GaAs pHEMT MMIC MEDIUM POWER AMPLIFIER, 6 - 18 GHz

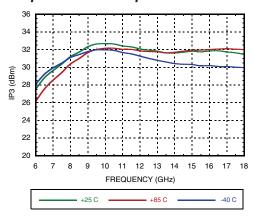
Power Compression @ 11 GHz



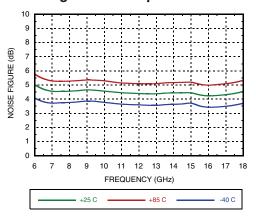
Power Compression @ 15 GHz



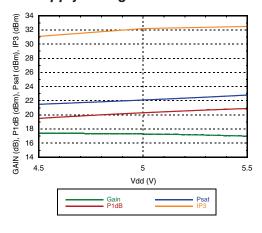
Output IP3 vs. Temperature



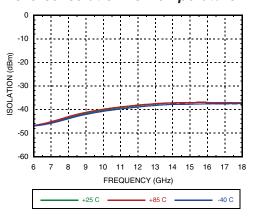
Noise Figure vs. Temperature



Gain, Power & Output IP3 vs. Supply Voltage @ 11 GHz



Reverse Isolation vs. Temperature

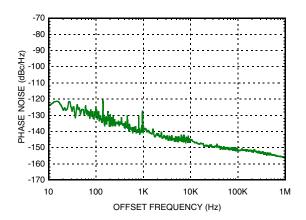




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Additive Phase Noise Vs Offset Frequency, RF Frequency = 8 GHz, RF Input Power = 5 dBm (P1dB)



Notes:



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Absolute Maximum Ratings

| Drain Bias Voltage (Vdd) | +6 Vdc |
|--|----------------------|
| RF Input Power (RFIN)(Vdd = +5 Vdc) | +15 dBm |
| Channel Temperature | 175 °C |
| Continuous Pdiss (T = 85 °C) (derate 8.2 mW/°C above 85 °C) | 0.74 W |
| Thermal Resistance (channel to ground paddle) | 122 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 0, Passed 100V |

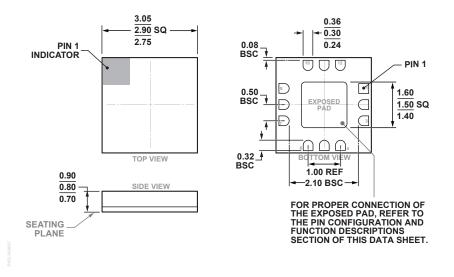
Typical Supply Current vs. Vdd

| Vdd (V) | Idd (mA) |
|---------|----------|
| +5.5 | 92 |
| +5.0 | 90 |
| +4.5 | 88 |

Note: Amplifier will operate over full voltage range shown above



Outline Drawing



12-Terminal Ceramic Leadless Chip Carrier [LCC] (E-12-4) Dimensions shown in millimeters

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking [2] |
|-------------|-----------------------|------------------|------------|---------------------|
| HMC441LC3B | Alumina, White | Gold over Nickel | MSL3 [1] | H441 XXXX |

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX



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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|-----------------|----------|---|---------------------|
| 1, 3, 7, 9 | GND | Package bottom must also be connected to RF/DC ground | ○ GND — |
| 2 | RFIN | This pin is AC coupled and matched to 50 Ohms. | RFIN ○── ├── |
| 4 - 6 10, 12 | N/C | This pin may be connected to RF/DC ground. Performance will not be affected. | |
| 8 | RFOUT | This pin is AC coupled and matched to 50 Ohms. | — —ORFOUT |
| 11 | Vdd | Power Supply Voltage for the amplifier. External bypass capacitors are required. | OVdd |

Application Circuit

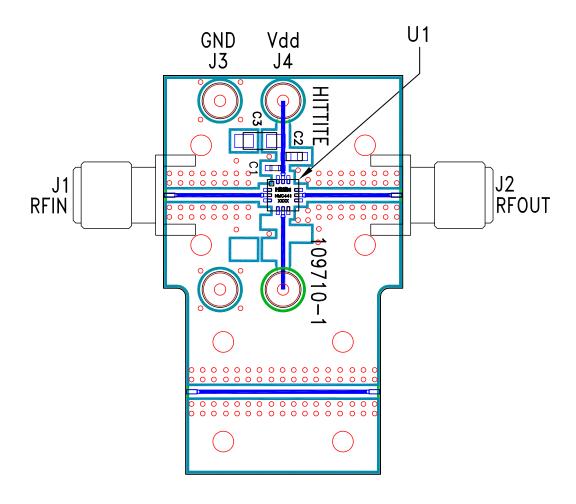
| Component C1 C2 C3 | Value 100 pF 1,000 pF 2.2 μF | Vdd C1 — C2 — C3 |
|--------------------|------------------------------|---|
| | | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ |
| F | RFIN > | 1 9 2 8 RFOUT 3 7 |
| | | 4 5 6 |



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Evaluation PCB



List of Materials for Evaluation PCB 109712 [1]

| Item | Description |
|---------|--------------------------------|
| J1 - J2 | PCB Mount SMA Connector |
| J3 - J4 | DC Pin |
| C1 | 100 pF Capacitor, 0402 Pkg. |
| C2 | 1000 pF Capacitor, 0603 Pkg. |
| C3 | 2.2 µF Capacitor, Tantalum |
| U1 | HMC441LC3B Amplifier |
| PCB [2] | 109710 Evaluation PCB, 10 mils |

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.

^[2] Circuit Board Material: Rogers 4350